Excellent Integrated System Limited

Stocking Distributor

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Vishay/Siliconix
SI2331DS-T1-E3

For any questions, you can email us directly:
sales@integrated-circuit.com

P-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 12	0.048 at V_{GS} = - 4.5 V	- 3.6
	0.062 at V_{GS} = - 2.5 V	- 3.2
	0.090 at V_{GS} = - 1.8 V	- 2.7

FEATURES

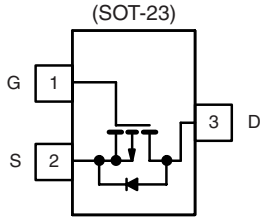
- **Halogen-free Option Available**
- TrenchFET® Power MOSFETS

Pb-free
RoHS COMPLIANT

APPLICATIONS

- Load Switch
- PA Switch

TO-236
(SOT-23)



Top View
Si2331DS *(E1)
* Marking Code

Ordering Information: Si2331DS-T1-E3 (Lead (Pb)-free)
Si2331DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**5 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	- 12		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	- 3.6	- 3.2	A
	T_A = 70 °C		- 2.9	- 2.6	
Pulsed Drain Current[a]		I_{DM}	- 12		
Continuous Source Current (Diode Conduction)[a]		I_S	- 0.74	- 0.59	
Power Dissipation[a]	T_A = 25 °C	P_D	0.89	0.71	W
	T_A = 70 °C		0.57	0.45	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 5 s	R_{thJA}	115	140	°C/W
	Steady State		140	175	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	60	75	

Notes:
a. Surface Mounted on FR4 board.
b. t ≤ 5 s.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm.

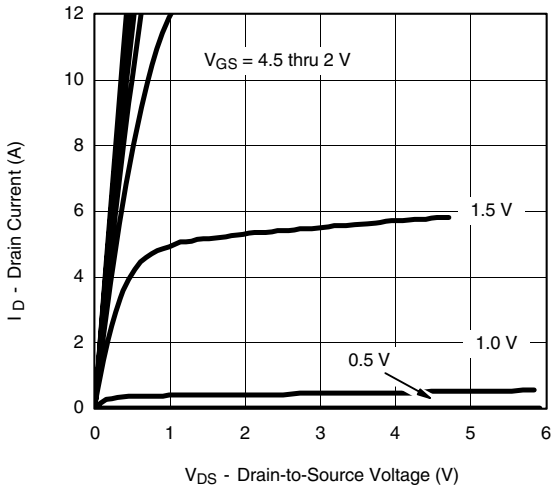
SPECIFICATIONS T_J = 25 °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Limits Min.	Limits Typ.	Limits Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = - 10 µA	- 12			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.45		- 0.90	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 12 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 12 V, V_{GS} = 0 V, T_J = 55 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 6			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 3.6 A		0.038	0.048	Ω
		V_{GS} = - 2.5 V, I_D = - 3.2 A		0.049	0.062	
		V_{GS} = - 1.8 V, I_D = - 2.7 A		0.070	0.090	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 5 V, I_D = - 3.6 A		3		S
Diode Forward Voltage	V_{SD}	I_S = - 1.6 A, V_{GS} = 0 V			- 1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = - 6 V, V_{GS} = - 4.5 V $I_D \cong$ - 3.6 A		9	14	nC
Gate-Source Charge	Q_{gs}			1.3		
Gate-Drain Charge	Q_{gd}			2.5		
Input Capacitance	C_{iss}	V_{DS} = - 6 V, V_{GS} = 0 V, f = 1 MHz		780		pF
Output Capacitance	C_{oss}			290		
Reverse Transfer Capacitance	C_{rss}			210		
Switching[b]						
Turn-On Time	$t_{d(on)}$	V_{DD} = - 6 V, R_L = 6 Ω $I_D \cong$ - 1.0 A, V_{GEN} = - 4.5 V R_G = 6 Ω		20	30	ns
	t_r			35	55	
Turn-Off Time	$t_{d(off)}$			65	100	
	t_f			50	75	

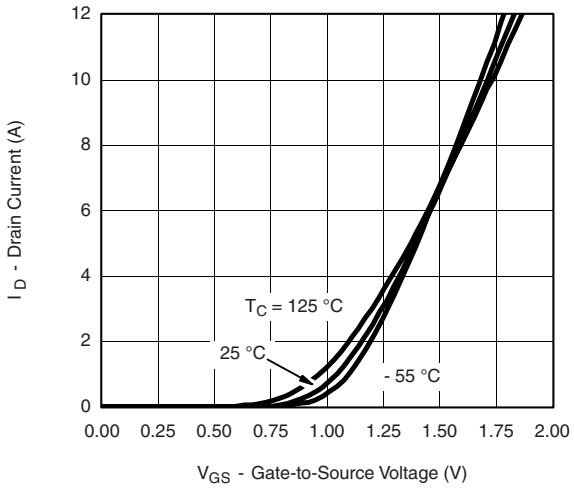
Notes:
a. For DESIGN AID ONLY, not subject to production testing.
b. Pulse test: PW ≤ 300 µs duty cycle ≤ 2 %.
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

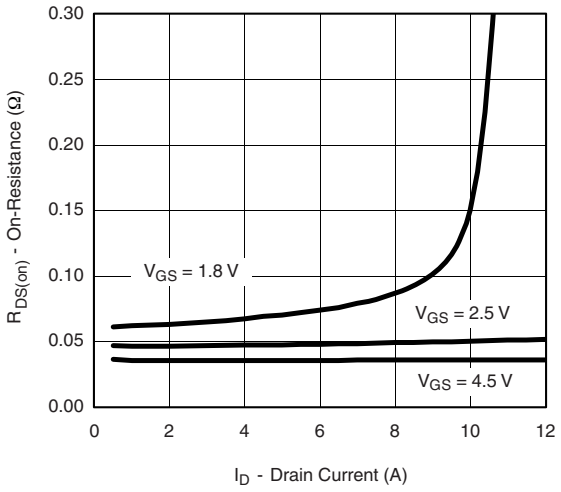
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



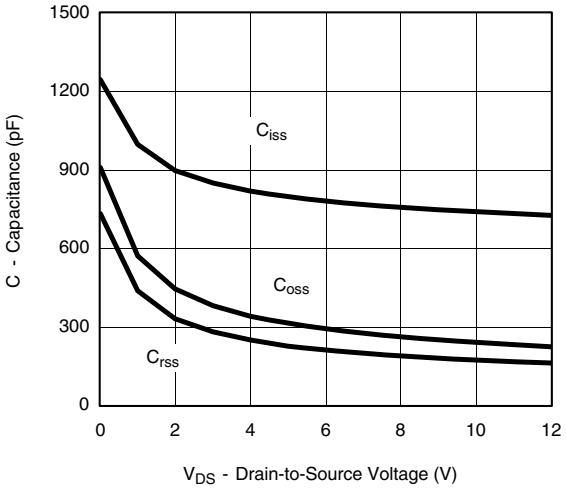
Output Characteristics



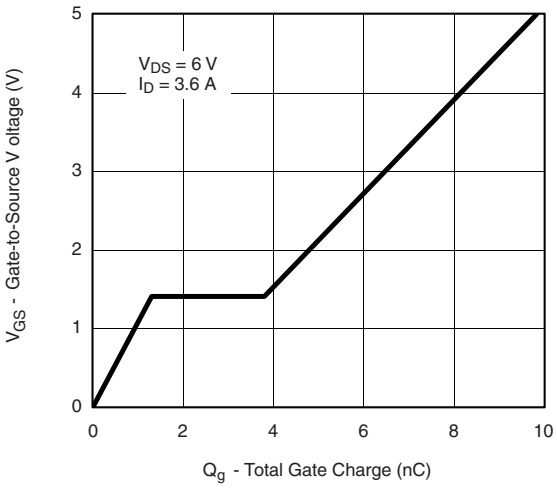
Transfer Characteristics



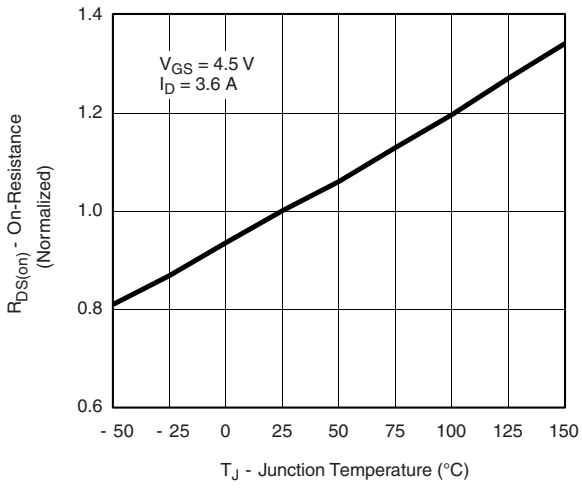
On-Resistance vs. Drain Current



Capacitance



Gate Charge

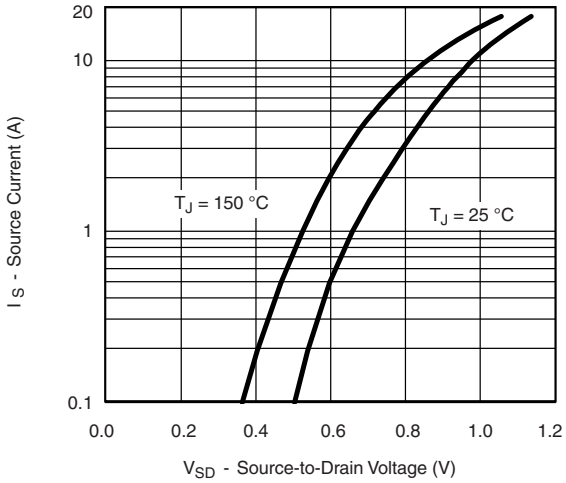


On-Resistance vs. Junction Temperature

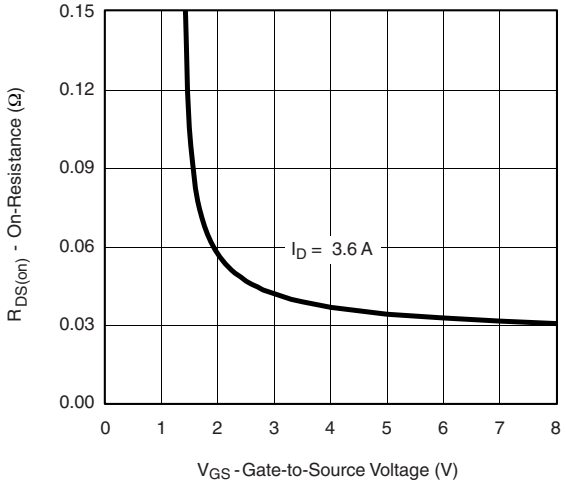
Si2331DS

Vishay Siliconix

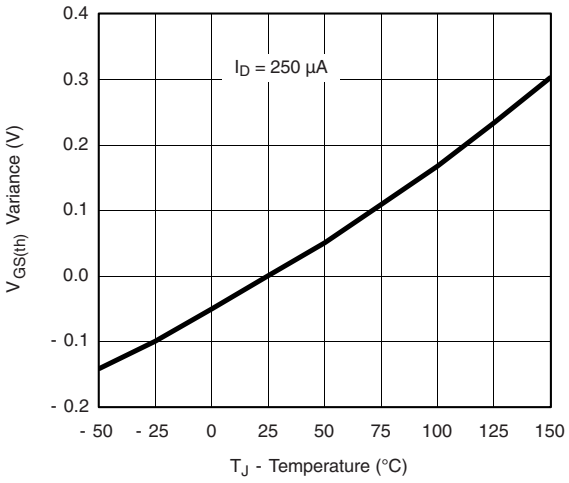
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



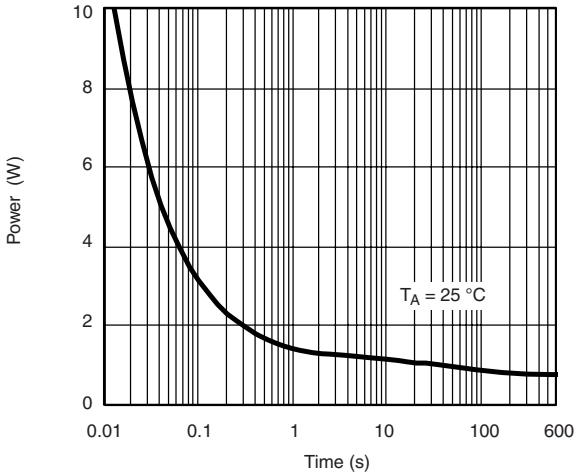
Source-Drain Diode Forward Voltage



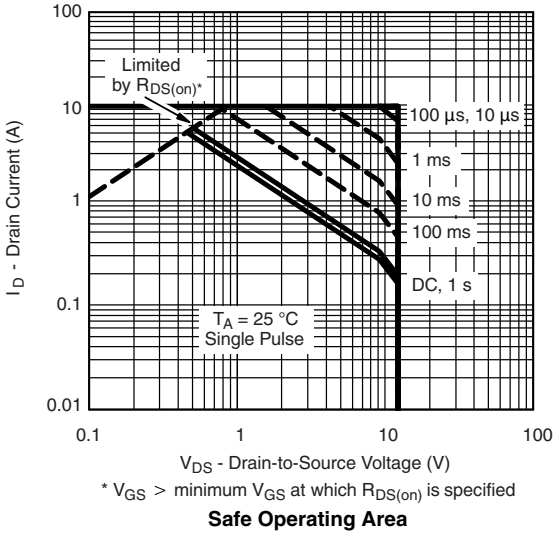
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



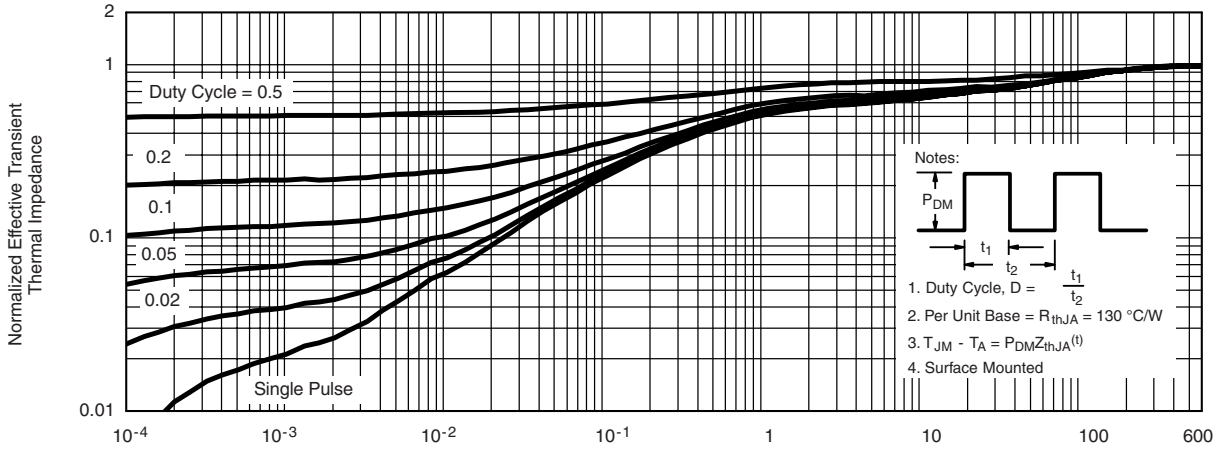
Single Pulse Power



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

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